

JP60211830

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FORMING METHOD FOR PATTERN

Abstract:

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PURPOSE:To control two-dimensional disposition of a monomolecular film or a monomolecular accumulation film by scanning a primary surface with atmospheric gas absence electron beam, then forming the monomolecular film or the monomolecular accumulation film and forming a pattern. **CONSTITUTION:**An SiO₂ film 1-2 is formed 30Angstrom thick as a primary surface on an Si (100) substrate 1-1, charged in an electron beam emission apparatus, the apparatus is evacuated to 1×10^{-6} Torr, the beam is scanned to evaporate the SiO₂ film on the primary surface to form a stripe pattern. Then, the primary surface is initially dipped in water, a monomolecular film of an arachidic acid is developed, and 9 layers are laminated under 30dyne/cm of surface pressure at 5cm/min of drawing speed. A monomolecular accumulation film 1-5 of arachidic acid is not formed on the portion of 1-4, but formed only on the portion of 1-3 according to the pattern. Thus, the primary surface is modified by the electron beam to form the sole molecular film or accumulation film in a pattern shape on the primary surface.

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